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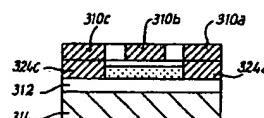
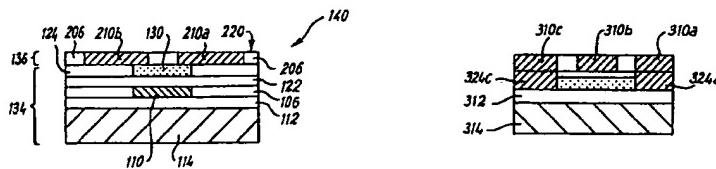
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(54) Title: A SEMICONDUCTOR DEVICE WITH METALLIC ELECTRODES AND A METHOD FOR USE IN FORMING SUCH A DEVICE



(57) Abstract: A semiconductor device comprising: a first electrode component; a second electrode component; a first layer comprising at least a portion of the first electrode component and at least a portion of the second electrode component; a second layer having a portion comprising deposited semiconductor material contacting the first and second electrode components; and a third layer comprising a substrate, wherein the first, second and third layers are arranged in order such that the second layer is positioned between the first layer and the third layer and wherein the first and second electrode components comprise electro-deposited metal. A method for use in forming a layered semiconductor device comprising: forming a transfer layer on a conductive carrier by the deposition of insulating material on the conductive carrier and then the electro-deposition of metal onto at least first and second portions of the conductive carrier, selectively exposed through the insulating material, to form first and second metal portions; fixing the transfer layer to a substrate portion of the device; and removing the conductive carrier from the device.

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